Configurable Multifunction Gate

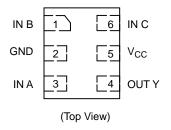
The NLX1G98 MiniGate[™] is an advanced high-speed CMOS multifunction gate. The device allows the user to choose logic functions MUX, AND, OR, NAND, NOR, INVERT and BUFFER. The device has Schmitt-trigger inputs, thereby enhancing noise immunity.

The NLX1G98 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

Features

- High Speed: $t_{PD} = 3.4 \text{ ns (Typ)} @ V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \mu A$ (Maximum) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra-Small Packages
- These are Pb-Free Devices

PIN ASSIGNMENTS





ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



UDFN6 1.0 x 1.0 CASE 517BX





UDFN6 1.2 x 1.0 CASE 517AA





UDFN6 1.45 x 1.0 CASE 517AQ



A = Specific Device Code M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

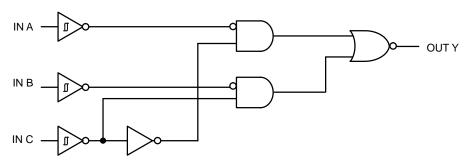


Figure 1. Function Diagram

PIN ASSIGNMENT

| 1 | IN B |
|---|-----------------|
| 2 | GND |
| 3 | IN A |
| 4 | OUT Y |
| 5 | V _{CC} |
| 6 | IN C |

FUNCTION TABLE*

| | Output | | |
|---|--------|---|---|
| Α | В | С | Υ |
| L | L | L | Н |
| L | L | Н | Н |
| L | Н | L | L |
| L | Н | Н | H |
| Н | L | L | Н |
| Н | L | Н | L |
| Н | Н | L | L |
| Н | Н | Н | L |

^{*}To select a logic function, please refer to "Logic Configurations section".

LOGIC CONFIGURATIONS

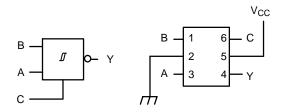


Figure 2. 2–Input MUX with Output Inverted

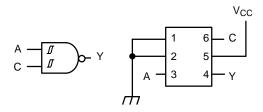


Figure 3. 2-Input NAND (When B = "L")

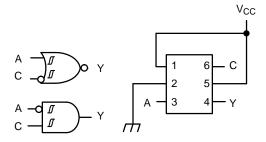


Figure 4. 2-Input NOR with Input C Inverted (When B = "H")

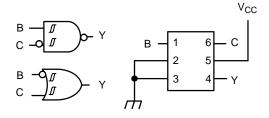


Figure 5. 2-Input NAND with Input C Inverted (When A = "L")

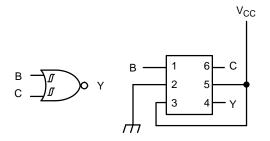


Figure 6. 2-Input NOR (When A ="H")

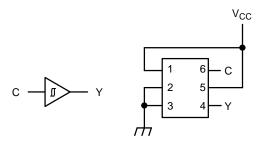


Figure 7. Buffer (When A = "L" and B = "H")

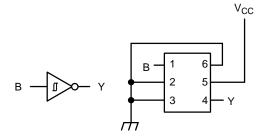


Figure 8. Inverter (When A = C = "L")

MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit | |
|----------------------|--|---|----------------------|------|--|
| V _{CC} | DC Supply Voltage | DC Supply Voltage | | | |
| V _{IN} | DC Input Voltage | | -0.5 to +7.0 | V | |
| V _{OUT} | DC Output Voltage | | -0.5 to +7.0 | V | |
| I _{IK} | DC Input Diode Current | V _{IN} < GND | -50 | mA | |
| I _{OK} | DC Output Diode Current | V _{OUT} < GND | -50 | mA | |
| Io | DC Output Source/Sink Current | ±50 | mA | | |
| Icc | DC Supply Current Per Supply Pin | | ±100 | mA | |
| I _{GND} | DC Ground Current per Ground Pin | | ±100 | mA | |
| T _{STG} | Storage Temperature Range | | -65 to +150 | °C | |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds | | 260 | °C | |
| TJ | Junction Temperature Under Bias | | 150 | °C | |
| MSL | Moisture Sensitivity | | Level 1 | | |
| F _R | Flammability Rating Oxygen | Index: 28 to 34 | UL 94 V-0 @ 0.125 in | | |
| V _{ESD} | Machi | dy Model (Note 2) ne Model (Note 3) ce Model (Note 4) | >2000 >200 N/A | V | |
| I _{LATCHUP} | Latchup Performance Above V _{CC} and Below GND at | 125°C (Note 5) | ±500 | mA | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm/2by/21 inch, 2 ounce copper trace no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Paramete | Parameter | | | |
|------------------|------------------------------------|--|-------------|----------------------------------|------|
| V _{CC} | Positive DC Supply Voltage | | 1.65 | 5.5 | V |
| V _{IN} | Digital Input Voltage | 0 | 5.5 | V | |
| V _{OUT} | Output Voltage | 0 | 5.5 | V | |
| T_A | Operating Free–Air Temperature | -55 | +125 | °C | |
| Δt/ΔV | Input Transition Rise or Fall Rate | $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$ | 0 0 0 | No Limit No Limit No Limit | nS/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

| | | | V _{CC} | 7 | Γ _A = 25° | C | T _A ≤ | +85°C | | 55°C to 25°C | |
|-----------------|--------------------------------|--|-----------------|--------------------------|----------------------|------|--------------------------|-------|--------------------------|-----------------|------|
| Symbol | Parameter | Conditions | (V) | Min | Тур | Max | Min | Max | Min | Max | Unit |
| V _{T+} | Positive | | 1.65 | 0.79 | | 1.16 | | 1.16 | | 1.16 | V |
| | Threshold Voltage | | 2.3 | 1.11 | | 1.56 | | 1.56 | | 1.56 | 1 |
| | | | 3.0 | 1.5 | | 1.87 | | 1.87 | | 1.87 | 1 |
| | | | 4.5 | 2.16 | | 2.74 | | 2.74 | | 2.74 | |
| | | | 5.5 | 2.61 | | 3.33 | | 3.33 | | 3.33 | |
| V_{T-} | Negative | | 1.65 | 0.35 | | 0.62 | 0.35 | | 0.35 | | V |
| | Threshold Voltage | | 2.3 | 0.58 | | 0.87 | 0.58 | | 0.58 | | 1 |
| | voltage | | 3.0 | 0.84 | | 1.19 | 0.84 | | 0.84 | | |
| | | | 4.5 | 1.41 | | 1.9 | 1.41 | | 1.41 | | |
| | | | 5.5 | 1.78 | | 2.29 | 1.78 | | 1.78 | | 1 |
| V_{H} | Hysteresis | | 1.65 | 0.30 | | 0.62 | 0.30 | 0.62 | 0.30 | 0.62 | V |
| | Voltage | | 2.3 | 0.40 | | 0.8 | 0.40 | 0.8 | 0.40 | 0.8 | 1 |
| | | | 3.0 | 0.53 | | 0.87 | 0.53 | 0.87 | 0.53 | 0.87 | 1 |
| | | | 4.5 | 0.71 | | 1.04 | 0.71 | 1.04 | 0.71 | 1.04 | 1 |
| | | | 5.5 | 0.8 | | 1.2 | 0.8 | 1.2 | 8.0 | 1.2 | 1 |
| V _{OH} | Minimum High-Level | $V_{IN} = V_{T-MIN} \text{ or } V_{T+MAX}$ $I_{OH} = -50 \mu\text{A}$ | 1.65 – 5.5 | V _{CC} - 0.1 | | | V _{CC} - 0.1 | | V _{CC} - 0.1 | | V |
| | Output Voltage | $V_{IN} = V_{T-MIN}$ or V_{T+MAX} | | | | | | | | | |
| | | $I_{OH} = -4 \text{ mA}$ | 1.65 | 1.2 | | | 1.2 | | 1.2 | | |
| | | $I_{OH} = -8 \text{ mA}$ | 2.3 | 1.9 | | | 1.9 | | 1.9 | | |
| | | I _{OH} = -16 mA | 3.0 | 2.4 | | | 2.4 | | 2.4 | | |
| | | $I_{OH} = -24 \text{ mA}$ | 3.0 | 2.3 | | | 2.3 | | 2.3 | | |
| | | $I_{OH} = -32 \text{ mA}$ | 4.5 | 3.8 | | | 3.8 | | 3.8 | | |
| V _{OL} | Maximum Low-Level | $V_{IN} = V_{T-MIN} \text{ or } V_{T+MAX}$ $I_{OL} = 50 \mu\text{A}$ | 1.65 – 5.5 | | | 0.1 | | 0.1 | | 0.1 | V |
| | Output Voltage | $V_{IN} = V_{T-MIN}$ or V_{T+MAX} | | | | | | | | | 1 |
| | | I _{OL} = 4 mA | 1.65 | | | 0.45 | | 0.45 | | 0.45 | |
| | | I _{OL} = 8 mA | 2.3 | | | 0.3 | | 0.3 | | 0.3 | |
| | | I _{OL} = 16 mA | 3.0 | | | 0.4 | | 0.4 | | 0.4 | |
| | | I _{OL} = 24 mA | 3.0 | | | 0.55 | | 0.55 | | 0.55 | 1 |
| | | I _{OL} = 32 mA | 4.5 | | | 0.55 | | 0.55 | | 0.55 | 1 |
| I _{IN} | Input Leakage Current | 0 ≤ V _{IN} ≤ 5.5 V | 0 to 5.5 | | | ±0.1 | | ±1.0 | | ±1.0 | μΑ |
| I _{CC} | Quiescent Supply Current | $V_{IN} = V_{CC}$ or GND | 5.5 | | | 1.0 | | 10 | | 10 | μΑ |

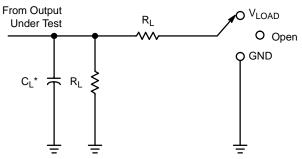
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

| | | | | 7 | Γ _A = 25°(| : | T _A ≤ | +85°C | | -55°C 25°C | |
|--------------------|--|---------------------|----------------|-----|-----------------------|----------|------------------|-------|-----|---------------|------|
| Symbol | Parameter | V _{CC} (V) | Test Condition | Min | Тур | Max | Min | Max | Min | Max | Unit |
| t _{PLH} , | Propagation Delay, | 1.65 – 1.95 | | 3.2 | 8.9 | 14.4 | 3.2 | 14.4 | 3.2 | 14.4 | ns |
| t _{PHL} | Any Input to Output Y (See Test Circuit) | 2.3 – 2.7 | | 2.0 | 5.2 | 8.3 | 2.0 | 9.0 | 2.0 | 9.3 | |
| | | 3.0 – 3.6 | | 1.5 | 4.0 | 7.2 | 1.5 | 7.5 | 1.5 | 7.8 | |
| | | 4.5 – 5.5 | | 1.1 | 3.4 | 5.8 | 1.1 | 6.1 | 1.1 | 6.5 | |
| C _{IN} | Input Capacitance | | | | 3.5 | | | | | | pF |
| C _{PD} | Power Dissipation Capacitance (Note 6) | 5.0 | f = 10 MHz | | 22 | | | | | | pF |

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption: P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

TEST CIRCUIT AND VOLTAGE WAVEFORMS



| Test | S 1 |
|------------------------------------|------------|
| t _{PLH} /t _{PHL} | Open |
| t _{PLZ} /t _{PZL} | V_{LOAD} |
| t _{PHZ} /t _{PZH} | GND |

Figure 9. Load Circuit

| | Inputs | | | | | | |
|-----------------|-----------------|--------------------------------|--------------------|---------------------|-------|---------|------------|
| V _{CC} | VI | t _r /t _f | V _M | V_{LOAD} | CL | R_{L} | V_Δ |
| 1.8 V ± 0.15 V | V _{CC} | ≤ 2 ns | V _{CC} /2 | 2 x V _{CC} | 30 pF | 1 kΩ | 0.15 V |
| 2.5 V ± 0.2 V | V _{CC} | ≤ 2 ns | V _{CC} /2 | 2 x V _{CC} | 30 pF | 500 Ω | 0.15 V |
| 3.3 V ± 0.3 V | 3 V | ≤ 2.5 ns | 1.5 V | 6 V | 50 pF | 500 Ω | 0.3 V |
| 5.5 V ± 0.5 V | V _{CC} | ≤ 2.5 ns | V _{CC} /2 | 2 x V _{CC} | 50 pF | 500 Ω | 0.3 V |

 $^{^{\}star}C_{L}$ includes probes and jig capacitance.

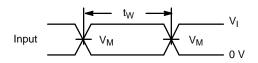


Figure 10. Voltage Waveforms Pulse Duration

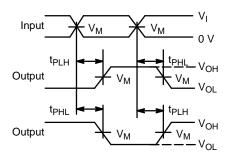


Figure 12. Voltage Waveforms Propagation Delay Times Inverting and Noninverting Outputs

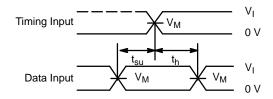


Figure 11. Voltage Waveforms Setup and Hold Times

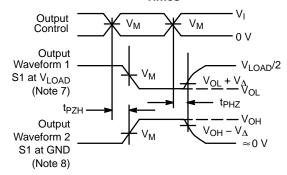


Figure 13. Voltage Waveforms Enable and Disable Times Low- and High-Level Enabling

- 7. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.
- 8. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control
- 9. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$.
- 10. The outputs are measured one at a time, with one transition per measurement.
- 11. All parameters are waveforms are not applicable to all devices.

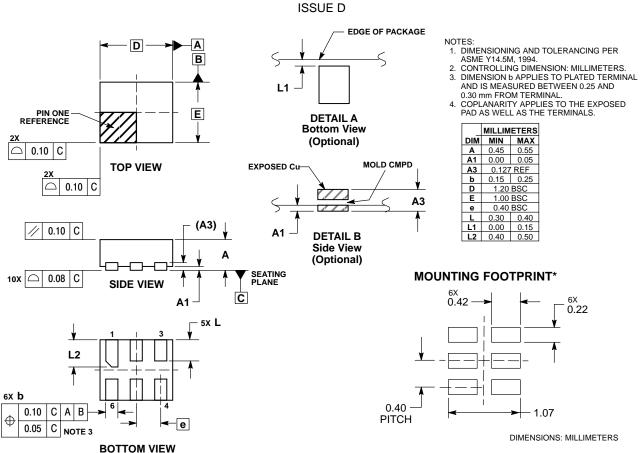
ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------------------------|--------------------------------------|-----------------------|
| NLX1G98MUTCG (In Development) | UDFN6, 1.2 x 1.0, 0.4P (Pb-Free) | 3000 / Tape & Reel |
| NLX1G98AMUTCG (In Development) | UDFN6, 1.45 x 1.0, 0.5P (Pb-Free) | 3000 / Tape & Reel |
| NLX1G98CMUTCG (In Development) | UDFN6, 1.0 x 1.0, 0.35P (Pb-Free) | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

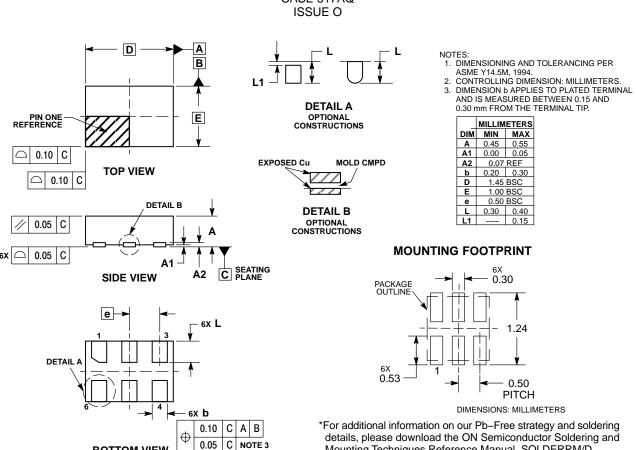
UDFN6, 1.2x1.0, 0.4P CASE 517AA-01



^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6 1.45x1.0, 0.5P CASE 517AQ

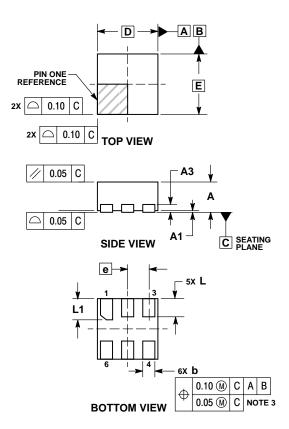


Mounting Techniques Reference Manual, SOLDERRM/D.

BOTTOM VIEW

PACKAGE DIMENSIONS

UDFN6 1.0x1.0. 0.35P CASE 517BX **ISSUE O**

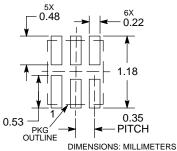


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF
- BURRS AND MOLD FLASH.

| | MILLIMETERS | | | | | |
|-----|-------------|------|--|--|--|--|
| DIM | MIN | MAX | | | | |
| Α | 0.45 | 0.55 | | | | |
| A1 | 0.00 | 0.05 | | | | |
| A3 | 0.13 REF | | | | | |
| b | 0.12 | 0.22 | | | | |
| D | 1.00 | BSC | | | | |
| E | 1.00 BSC | | | | | |
| е | 0.35 BSC | | | | | |
| L | 0.25 | 0.35 | | | | |
| L1 | 0.30 | 0.40 | | | | |

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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